



# ACE14201T

## P-Channel Enhancement Mode Power MOSFET

### Description

The ACE14201T uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### Features

- $V_{DS} (V) = -20V$   $I_D = -14A$
- $R_{DS(ON)} \leq 8.5m\Omega$  ( $V_{GS} = -4.5V$ )
- $R_{DS(ON)} \leq 12m\Omega$  ( $V_{GS} = -2.5V$ )
- $R_{DS(ON)} \leq 17m\Omega$  ( $V_{GS} = -1.8V$ )

### Absolute Maximum Ratings @ $T_A=25^\circ C$ unless otherwise noted

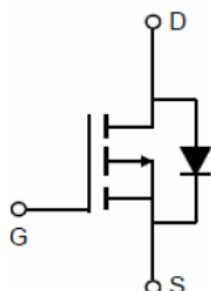
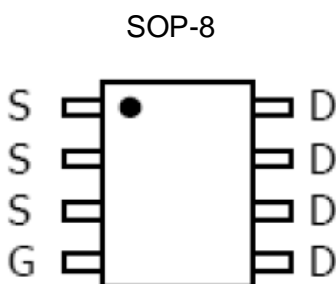
Parameter	Symbol	Max	Unit
Drain-Source Voltage	$V_{DSS}$	-20	V
Gate-Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (Continuous)*AC	$I_D$	$T_A=25^\circ C$	-14
		$T_A=100^\circ C$	-8.8
Drain Current (Pulsed)*B	$I_{DM}$	-56	A
Avalanche energy $L=0.1mH$	$E_{AS}, E_{AR}$	22	mJ
Power Dissipation	$T_A=25^\circ C$	$P_D$	2
Operating temperature / storage temperature	$T_J/T_{STG}$	-55~150	$^\circ C$
Thermal Resistance ,Junction-to-Ambient*	$R_{\theta JA}$	62	$^\circ C/W$

A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ C$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the  $t \leq 10s$  junction to ambient thermal resistance rating.

### Packaging Type



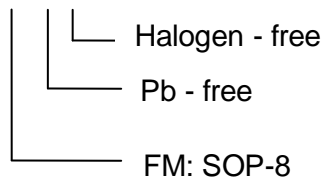


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### Ordering information

ACE14201T XX + H



### Electrical Characteristics $T_A=25^{\circ}\text{C}$ , unless otherwise specified.

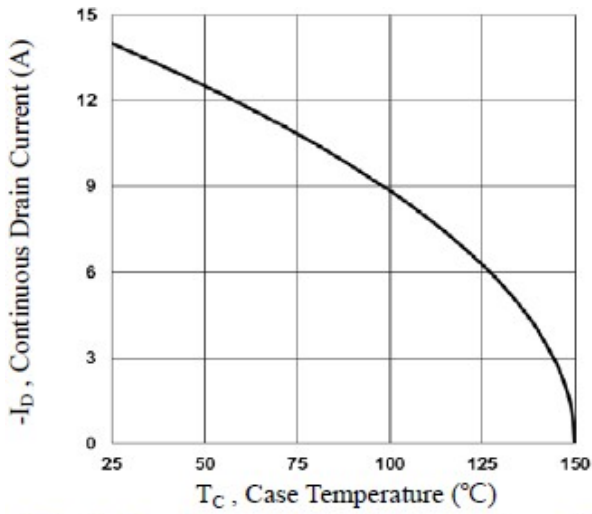
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$			-1	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_{DS}=-250\mu A$	-0.3	-0.6		V
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 12V, V_{DS}=0V$			$\pm 100$	nA
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-8A$		6.5		m $\Omega$
		$V_{GS}=-2.5V, I_D=-5A$		9		
		$V_{GS}=-1.8V, I_D=-3A$		12		
Forward trans conductance	$g_{FS}$	$V_{DS}=-10V, I_D=-5A$		20		S
Diode forward voltage	$V_{SD}$	$I_{SD}=-1A, V_{GS}=0V$			-1.2	V
Switching						
Total gate charge	Qg	$V_{GS}=-4.5V, V_{DS}=-10V, I_D=-5A$		44.4		nC
Gate-source charge	Qgs			7.2		
Gate-drain charge	Qgd			10.2		
Turn-on delay time	$t_{d(on)}$	$V_{GS}=-10V, V_{DD}=-15V,$ $I_D=-1A, R_{GEN} = 6\Omega$		13.2		ns
Turn-on rise time	Tr			68		
Turn-off delay time	$t_{d(off)}$			160		
Turn-off fall time	Tf			154		
Dynamic						
Input capacitance	Ciss	$V_{GS}=0V, V_{DS}=-15V, f=1.0MHz$		4060		pF
Output capacitance	Coss			520		
Reverse transfer capacitance	Crss			400		



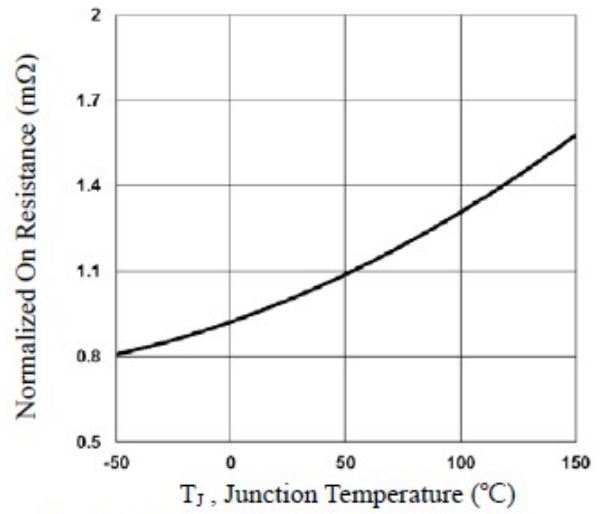
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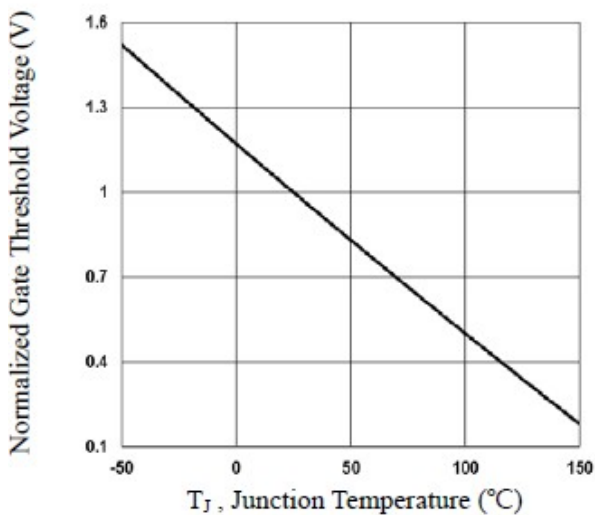
### Typical Performance Characteristics



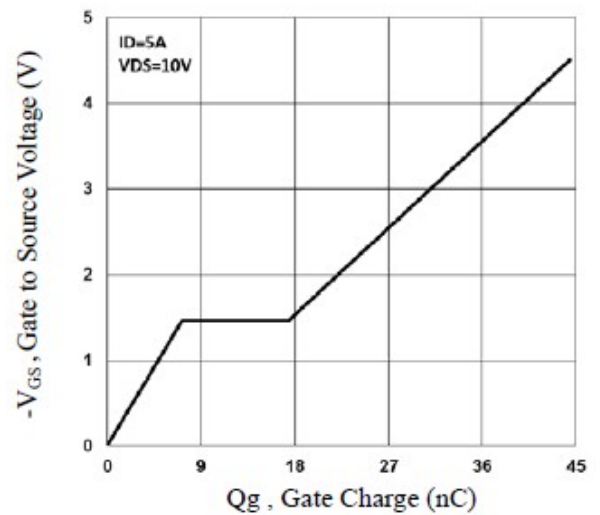
**Fig.1 Continuous Drain Current vs.  $T_c$**



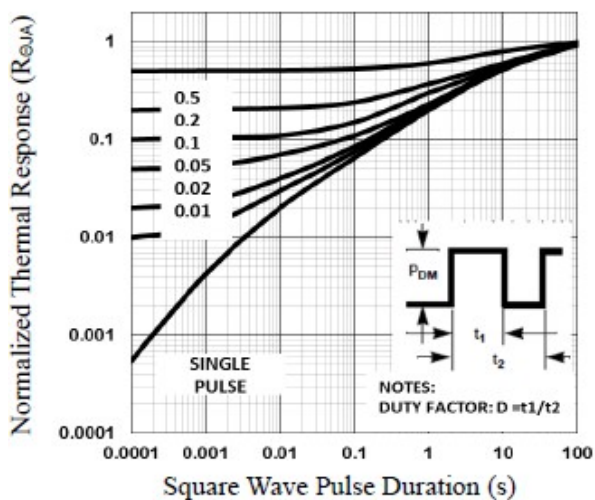
**Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_j$**



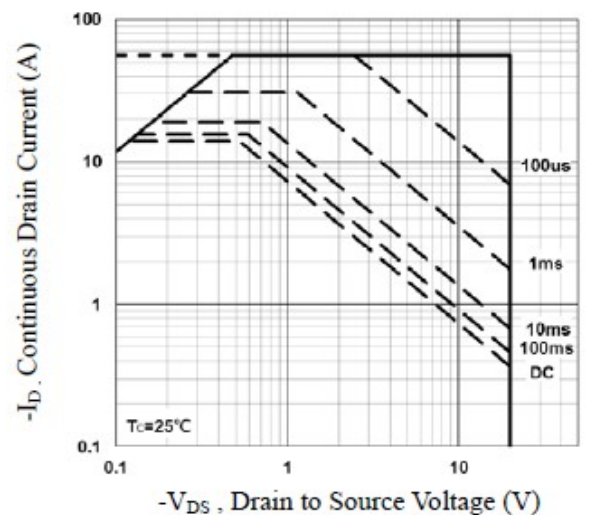
**Fig.3 Normalized  $V_{th}$  vs.  $T_j$**



**Fig.4 Gate Charge Waveform**



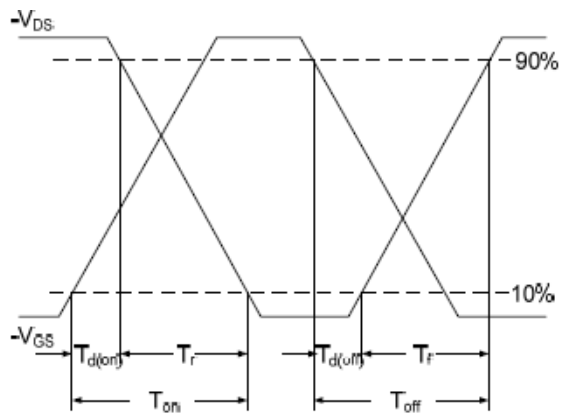
**Fig.5 Normalized Transient Response**



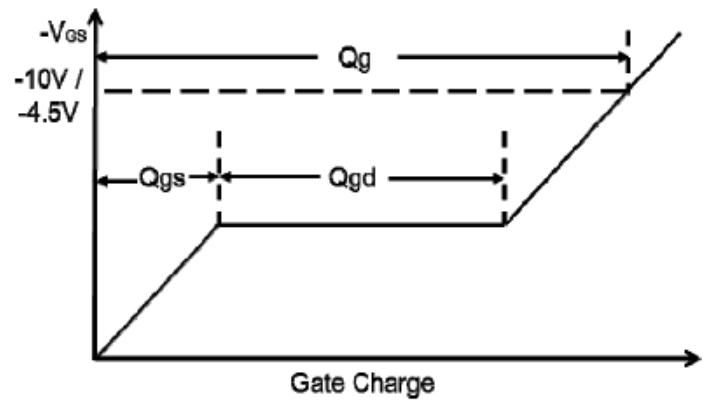
**Fig.6 Maximum Safe Operation Area**



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**Fig.7 Switching Time Waveform**



**Fig.8 Gate Charge Waveform**

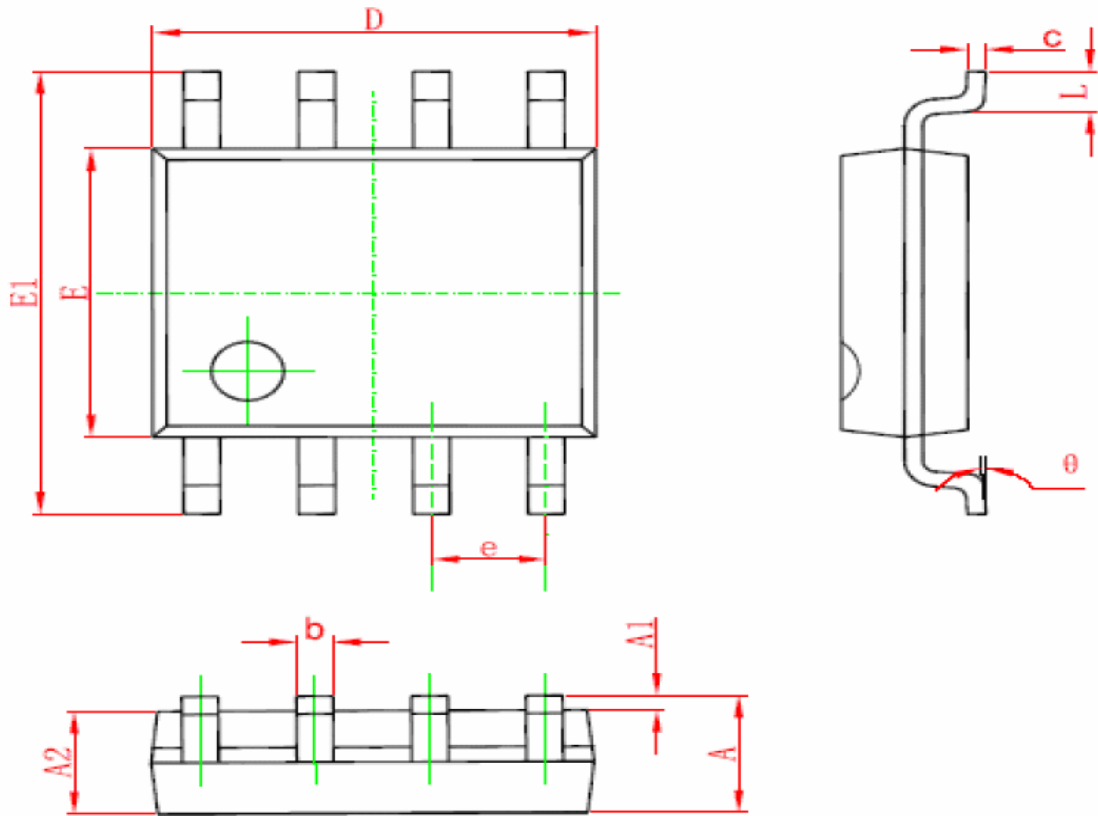


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### Packing Information

#### SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
theta	0°	8°	0°	8°



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### Notes

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1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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